

ABSTRACT OF THE DISCLOSURE

A high frequency power amplifier module of a multistage amplifier construction comprising: an input terminal; an output terminal; a control terminal; and 5 a mode switching terminal. The first amplification stage includes a dual gate FET, and a bias voltage according to a signal is applied to the first gate and the second gate of the dual gate FET from the control terminal and the mode switching terminal, and a radio 10 signal from the input terminal is applied to the second gate such as the source of the dual gate FET. In dependence upon the signal from the mode switching terminal, the mode of the high frequency power amplifier module is for the GSM (i.e., for a non- 15 linear amplifying action) and for the EDGE (for a linear amplifying action).